	ESC	<u>;</u>	D	OCUMENT	CHANGE REQUEST
DCR number	396	Changes re	quired for: N/A	۱.	Originator: Samuel SAVIN
Date: 2008/02	2/28	Date sent: 2	2008/02/28		Organisation: CNES
Status: IMPLE	MENTED				
Title:	Diodes, Power Re	ctifier, High Eff	iciency Fast Re	covery , based or	туре ВҮV 54-200
Number:	5103/031		Issue:	3	
Other document	ts affected:			•	
Page:					
Paragraph 1.4.2 Paragraph 1.5, Paragraph 1.8, Paragraph 2.4.2 Paragraph 2.4.2 Paragraph 2.4.3 Paragraph 2.5, Paragraph 2.6, Paragraph: Paragraph 1.4.2	2, page 5 page 6 page 7 1, page 9 2, page 9 3, page 9 page 10 page 10 2, page 5				
Paragraph 1.5, Paragraph 1.8, Paragraph 2.4.2 Paragraph 2.4.2 Paragraph 2.4.3 Paragraph 2.5, Paragraph 2.6, Original wording	page 6 page 7 1, page 9 2, page 9 3, page 9 page 10 page 10 g:				
Proposed wordi	ng:				
See attached de	ocument				
Justification:					
New variant 02 New variant 03 need. Paragraph 1.5 I	(hot solder dip) int (gold finish) and 04 MAXIMUM RATING	roduction with (hot solder dip S correction e	TO254 package b) introduction error of note 3 fe	e for European cu with TO254AA lov or variant 01 and (stomers need. v ohmic package for European customers 02 (see explanation on attached
document) and	new derating adde	d for variant 03	and 04 in the r	note 3.	

E	<u>SC</u>	C	DOCUMENT	CHANGE REQUEST				
DCR number	396	Changes required for:	N/A	Originator: Samuel SAVIN				
Date: 2008/02/28		Date sent: 2008/02/28		Organisation: CNES				
Status: IMPLEMENTE	ED							
Attachments:								
DCR396markup.pdf, D	CR396att.pdf	, null						
Modifications:								
Pages affected: 5, 6, 7, 9, 10, 11 Paras affected: 1.4.2, 1.5, 1.6, 1.7, 1.8, Proposed Wording of C See attached hand mai Summary of changes: - Addition of new varia - Io derating in Para 1. - Forward Voltage limit is added with applicable	DCR details are replaced by the following as discussed and agreed with the Manufacturer ST: Pages affected: 5, 6, 7, 9, 10, 11 Paras affected: 1.4.2, 1.5, 1.6, 1.7, 1.8, 2.4.1, 2.4.2, 2.4.3, 2.5, 2.6, 2.7, 2.8 							
 Justification Introduction of new variants 02 to 05 for European customer. Io derating for variant 01 (& 02, 03) is amended in order to correct a previous calculation error: Max power derating = Tj - (lo x Vf x Rth(j-c)) = 150 - (40 x 1.5 x 1) = 90C (not 110C) Forward Voltage in Para 2.6 for variant 01 (& 02, 03) is amended to correct a previous typographic error. 								
Approval signature:								
R.C. Har	1_1							
Date signed:								
2008-02-28								

1.4.2 Component Type Variants

Variant	Based on Type	Case	Description	Lead Material	Weight
Number				and Finish	Max g
01	BYV54-200	TO254	Single diode	H9	10
02	BYV54-200	TO254	Single diode	H4	10
03	BYV54-200	TO254AA	Single diode	S 9	10
04	BYV54-200	TO254AA	Single diode	S 4	10

Justification :

Variant 02: new variant introduction with TO254 package for European customer Variant 03: new variant introduction with TO254AA low ohmic package for European customer

Variant 04: new variant introduction with TO254AA low ohmic package for European customer

1.5 MAXIMUM RATINGS

NOTES

3. At $T_{case} > +90^{\circ}C$, derate linearly to 0A at +150°C for variant 01 and variant 02.

At $T_{case} > +99^{\circ}C$, derate linearly to 0A at $+150^{\circ}C$ for variant 03 and 04.

Justification :

For variant 01 and 02 Calcul of the derating is wrong: For max rating 40A we have used f max at 30A instead of 40A with I0 max at 30A. The right calculation is: for I0 max 40A, Vf max = 1.5V (issued from ST data characterization). Formula applied: Max power derating = Tj – (Io x Vf x Rth(j-c)) = $150 - (40 \times 1.5 \times 1) = 90^{\circ}$ C

The new limit for the derating is 90°C

For variant 03 and 04 Max power derating = Tj – (Io x Vf x Rth(j-c)) = $150 - (40 \times 1.26 \times 1) = 99^{\circ}C$

1.8 FUNCTIONAL DIAGRAM

Variant 01 and variant 02

Terminal 1 : Cathode Terminal 2 : N.C. Terminal 3 : Anode



Variant 03 and 04

Terminal 1 : Cathode Terminal 2 : Anode Terminal 3 : Anode



Justification :

Variant 02: new variant introduction with TO254 package for European customer Variant 03: new variant introduction with TO254AA low ohmic package for European customer

Variant 04: new variant introduction with TO254AA low ohmic package for European customer

2.4.1 ROOM TEMPERATURE ELECTRICAL MEASUREMENTS

CHARACTERISTICS	SYMBOL	MIL-STD-750	TEST CONDITIONS	DITIONS LIMITS		UNIT
		TEST METHOD	Note 5	MIN.	MAX.	
Forward Voltage	V _{F1}	4011	Pulse Method	-		V
			I _F = 20 A, Note 1			
			Variant 01 and 02		1.1	
			Variant 03 and 04		0.95	
	V _{F2}	4011	Pulse Method	-		V
			I _F = 30 A, Note 1			
			Variant 01 and 02		1.3	
			Variant 03 and 04		1.1	

Justification :

Variant 02: new variant introduction with TO254 package for European customer Variant 03: new variant introduction with TO254AA low ohmic package for European customer

Variant 04: new variant introduction with TO254AA low ohmic package for European customer

CHARACTERISTICS	SYMBOL	MIL-STD-750	TEST CONDITIONS	LIM	IITS	UNIT
		TEST METHOD	Note 4 and 5	MIN.	MAX.	
Forward Voltage	V _{F1}	4011	$T_{case} = +125(+0.5)^{\circ}C$	-		V
			Pulse Method			
			I _F = 20 A, Note 1			
			Variant 01 and 02		1	
			Variant 03 and 04		0.85	
			$T_{case} = -55(+5 - 0)^{\circ}C$			V
			Pulse Method			
			I _F = 20 A, Note 1			
			Variant 01 and 02		1.3	
			Variant 03 and 04		1.15	
	V _{F2}	4011	$T_{case} = +125(+0.5)^{\circ}C$	-		V
			Pulse Method			
			I _F = 30 A, Note 1			
			Variant 01 and 02		1.1	
			Variant 03 and 04		1	

2.4.2 HIGH AND LOW TEMPERATURES ELECTRICAL MEASUREMENTS

Justification :

Variant 02: new variant introduction with TO254 package for European customer Variant 03: new variant introduction with TO254AA low ohmic package for European customer

Variant 04: new variant introduction with TO254AA low ohmic package for European customer

2.4.3 Notes to Electrical Measurements Tables note 5 added: For Variant 03 and 04 measurement done when pin 2 and 3 tied together.

Justification :

Variant 02: new variant introduction with TO254 package for European customer Variant 03: new variant introduction with TO254AA low ohmic package for European customer

Variant 04: new variant introduction with TO254AA low ohmic package for European customer

2.5 PARAMETER DRIFT VALUES

note 2 added: For Variant 03 and 04 measurement done when pin 2 and 3 tied together.

Justification :

Variant 03: new variant introduction with TO254AA low ohmic package for European customer Variant 04: new variant introduction with TO254AA low ohmic package for European customer

2.6 INTERMEDIATE AND END-POINTS ELECTRICAL MEASUREMENTS

CHARACTERISTICS	SYMBOL	LIMITS		UNITS
		MIN.	MAX.	
Forward Voltage 1	V _{F1}	-		V
Variant 01 and 02			1.1	
Variant 03 and 04			0.95	

note 1 added: For Variant 03 and 04 measurement done when pin 2 and 3 tied together.

Justification :

Variant 02: new variant introduction with TO254 package for European customer Variant 03: new variant introduction with TO254AA low ohmic package for European customer

Variant 04: new variant introduction with TO254AA low ohmic package for European customer





Pages 1 to 12

DIODES, POWER RECTIFIER, HIGH EFFICIENCY, FAST

RECOVERY

BASED ON TYPE BYV54-200

ESCC Detail Specification No. 5103/031

4 July 2008 Issue 3 April 2007

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Document Custodian: European Space Agency - see https://escies.org



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ESCC Detail Specification No. 5103/031

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ISSUE \$ 4 (on all pages)

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DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
287	Specification up issued to incorporate editorial and technical changes per DCR.
296	



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APPENDIX 'A'



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1. <u>GENERAL</u>

1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 <u>APPLICABLE DOCUMENTS</u>

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 <u>TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS</u>

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u>

The ESCC Component Number shall be constituted as follows: Example: 510303101

- Detail Specification Reference: 5103031
- Component Type Variant Number: 01 (as required)

1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Description	Lead Material and Finish	Weight max g
01	BYV54-200	TO-254	Single diode	H9	10

Add varions 02605 see attached

The lead material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage. Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Forward Surge Current	IFSM	400	A	Note 1
Repetitive Peak Reverse Voltage	V _{RRM}	200	V	Note 2

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Para 1.4.2 Component Type Variants

Variant Number	Based on Type	Case	Description	Lead Material and Finish	Weight Max g
01	BYV54-200	TO-254	Single diode	Н9	10
02	BYV54-200	TO-254	Single diode	H14	10
03	BYV54-200	TO-254	Single diode	H4	10
04	BYV54-200	TO-254AA	Single diode-Low Ohmic Package	S14	10
05	BYV54-200	TO-254AA	Single diode-Low Ohmic Package	S4	10



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Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Average Output Rectified Current	I _O	40	A	50% Duty Cycle Note 3
RMS Forward Current	I _{F(rms)}	60	A	······
Operating Temperature Range (Case Temperature)	T _{op}	-55 to +150	°C	Note 4
Junction Temperature	Тj	+150	°C	
Storage Temperature Range	T _{stg}	-55 to +150	°C	Note 4
Soldering Temperature	T _{sol}	+260	°C	Note 5
Thermal Resistance, Junction to Case	R _{th(j-c)}	1	°C/W	Note 6

NOTES:

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01,03,05,

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- 1. Sinusoidal pulse of 10ms duration.
- 3. At Tcase >+90°C, denote linearly to OA at +150°C for Variants 01,02,03
- 2. Pulsed, duration 5ms, f = 50Hz.
- Pulsed, duration 5ms, f = 50Hz. At Tcase > +990°C, derate linearly to OA at +150°C. for Variants 04,05 To Variants 04,05 3.
- 4. For Variants, with hot solder dip lead finish, all testing performed at Tamb > +125°C shall be carried out in a 100% inert atmosphere.
- Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the 5. same lead shall not be resoldered until 3 minutes have elapsed.
- Package mounted on an infinite heatsink. 6.

and TO-254AA packages

HANDLING PRECAUTIONS

The TO-254/package contain Beryllium Oxide (BeO) and therefore K must not be ground, machined, sandblasted or subjected to any mechanical operation which will produce dust. The case must not be subjected to any chemical process (e.g. etching) which will produce fumes.





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Ormhala	Dimensio	ons mm	Notes
Symbols	Min	Max de la com	
A	13.59	13.84	
В	13.59	13.84	
С	20.07	20.32	
D	6.3	6.7	
E	1	1.35	
ØF	3.5	3.9	
G	16.89	17.4	
Н	6.86	BSC	
ØI	0.89	1.14	2
J	3.81	BSC	
К	3.81	BSC	
L	12.95	14.5	
ØM	3.05 T	ypical	2
N	-	0.71	2
R1	-	1	3
R2	1.65 T	ypical	4

NOTES:

- 1. The terminal identification is specified by the components geometry. See Functional Diagram for the terminal connections.
- 2. 3 places.
- 3. Radius of heatsink flange corner, 4 places.
- 4. Radius of body corner, 4 places.

1.8 FUNCTIONAL DIAGRAM

Variants01,02,03

NOTES:

1. The case is not connected to any lead.

Terminal 1: Cathode

Terminal 3: Anode

MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case

The case shall be hermetically sealed and have a metal body. The leads pass through ceramic eyelets brazed into the frame and the lid shall be welded.

Add New figure-see attached)

1.9

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Para 1.8

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Variants 04,05

Terminal 1: Cathode Terminal 2: Anode Terminal 3: Anode





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b) Leads

As specified in Component Type Variants.

REQUIREMENTS 2.

GENERAL 2.1

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

- Deviations from the Generic Specification 2.1.1
- Deviations from Qualification and Periodic Tests Chart F4 2.1.1.1
 - (a) Constant Acceleration is not applicable.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number.
- (c) Traceability information.
- (d) Warning sign for Berryllium Oxide.
- 2.3 TERMINAL STRENGTH

The test conditions for Terminal Strength, tested as specified in the ESCC Generic Specification, shall be as follows:

Test Condition: A, tension, with an applied force of 10N for a duration of 10s.

- ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES 2.4 Electrical measurements shall be performed at room, high and low temperatures. Consolidated notes are given after the Tables.
- 2.4.1 **Room Temperature Electrical Measurements** The measurements shall be performed at T_{amb} =+22 ±3°C.



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of (see champes as attacked)

Characteristics	Symbols	MIL-STD-750	Test Conditions	Lin	nits	Units
		iest Mietnod	(Note 1)	Min	Max	
Reverse Current	I _R	4016	DC Method V _R = 200V	-	50	μΑ
Forward Voltage	V _{F1}	4011 *	Pulse Method I _F =20A, Note オス	-	1.1 0.95	V
	V _{F2}	4011	Pulse Method I _F =30A, Note X2	-	1.3 I · I	V
Breakdown Voltage	V _(BR)	4021	I _R = 100μΑ	200	-	V
Capacitance	С	4001	V _R = 10V f = 1MHz	-	400	рF
Reverse Recovery Time	t _{rr}	4031	Test Condition A I _F =1A V _B = 30V dI _F /dt=-50A/μs	-	60	ns
Thermal Impedance, Junction to Case	Z _{th(j-c)}	3101	I _H = 15V to 40A t _H = 50ms I _M = 50mA t _{md} = 100μs Note 2 3	(Calcula see N	ate ∆V _F , lote β) 4-	°C/W

2.4.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750	Test Conditions	Lin	nits	Units
	1998년 1997년 1997년 - 1997년 19 1997년 1997년 199	lest Method		^{ia} Min	Max	1144
Reverse Current	1 ₈	4016	T_{case} =+125(+0 -5)°C DC Method V _R = 200V	-	40	mA
Forward Voltage	V _{F1}	4011	$T_{case} = +125(+0.5)^{\circ}C$ Pulse Method $I_F = 20A$, Note 2	-	1 0.85	V
		*	T_{case} =-55(+5 -0)°C Pulse Method I _F =20A, Note 1 2		1.3 1.15	V
	V _{F2}	4011	T _{case} =+125(+0 -5)°C Pulse Method I _F = 30A, Note <i>Y ⋧</i>		1.1 <u>1</u>	V

2.4.3

* (see chamages as ottached)

- Notes to Electrical Measurement Tables
 - **2** \varkappa . Pulsed Width \leq 300 μ s, Duty Cycle \leq 2%.
 - 3 2. Performed only during Screening Tests Parameter Drift Values (Initial Measurements), go-no-go.
 - 4.8. The limits for ΔV_F shall be defined by the manufacturer on every lot in accordance with MIL-STD-750 Method 3101 and shall guarantee the $R_{th(j-c)}$ limits specified in Maximum Ratings.
 - 5 A. Read and record measurements shall be performed on a sample of 5 components with 0 failures
 - 1. For Variants 04,05 testing shall be performed with both anode terminals Dance 3 tied bogether

Characteristics	Symbols	MIL-STD-750	Test Conditions	Lin	nits	Units
		Test Method	(Note 1)	Min	Max	
 Forward Voltage 1	V _{F1}	4011	Pulse Method	-		V
			I _F = 20 A, Note 2			
			Variants 01, 02, 03		1.1	
			Variants 04, 05		0.95	
 Forward Voltage 2	V _{F2}	4011	Pulse Method	- 1		V
	• -		I _F = 30 A, Note 2			
			Variant 01 to 03		1.3	
			Variant 04 and 05		1.1	

Para 2.4.1 Room Temperature Electrical Measurements

Para 2.4.2 High and Low Temperature Electrical Measurements

Characteristics	Symbols	MIL-STD-750	Test Conditions	Lin	nits	Units
		Test Method	(Notes 1, 5)	Min	Max	
Forward Voltage 1	V _{F1}	4011	$T_{case} = +125(+0.5)^{\circ}C$	-		V
			Pulse Method			
			I_F = 20 A, Note 2 Variants 01, 02, 03 Variants 04, 05		1 0.85	
			$T_{case} = -55(+5 - 0)^{\circ}C$			V
			Pulse Method			
			I_F = 20 A, Note 2 Variants 01, 02, 03 Variants 04, 05		1.3 1.15	
Forward Voltage 2	V _{F2}	4011	$T_{case} = +125(+0.5)^{\circ}C$	-		V
			Pulse Method			
			I _F = 30 A, Note 2 Variants 01, 02, 03		1.1	
			Variants 04, 05			



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allowed. Alternatively a 100% inspection may be performed.

2.5

PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (A) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols		Limits		Units
		Drift	Abs	olute	
		Value A	Min	Max	
Reverse Current	I _R	±6 or (1) ±100%	-	50	μA
Forward Voltage 1	V _{F1}	±0.07	-	1.1	V
0TES.					0.95

* See chruses as attached

NOTES:

1. Whichever is the greater referred to the initial value.

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 ±3°C. The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements . The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Lin	nits	Units
		Min	Max	
Reverse Current	I _R	-	50	μΑ
Forward Voltage 1	V _{F1}	-	1 K	V
x <	VE2	1 *	J&	*

(see changes attached And VF2)

2.7

HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

Characteristics	Symbols	Limits 1997	Units
Ambient Temperature	T _{amb}	+150 (+0 -5)	°C
Reverse Voltage	V _R	160	V
Duration	t	≥48	hours

NOTES:

1. For Variants 04,05 testing shall be performed with both anode terminals 2 and 3 fied together.

Para 2.5 PARAMETER DRIFT VALUES

Characteristics	Symbols	mbols Limits			Units	
		Drift	Abs	olute		
			Min	Max		
Forward Voltage 1 Variants 01, 02, 03 Variants 04, 05	V _{F1}	± 0.07		1.1 0.95	V	

Para 2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Characteristics	Symbols	Limits		Units
		Min	Max	
Forward Voltage 1	VF1	-		V
Variants 01, 02, 03			1.1	
Variants 04, 05			0.95	
Forward Voltage 2	VF2	-		V
Variants 01, 02, 03			1.3	
Variants 04, 05			1.1	



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2.8 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Case Temperature	T _{case}	+125 ±15, Note 1	°C
Junction Temperature	Τj	+150 (+0 -5)	°C
Average Output Rectified Current	۱ ₀	≥ 10, Note 1	А

NOTES:

- 1. The case temperature and/or output current may be adjusted, within their given limit ranges, to attain the specified junction temperature.
- 2. For Variants 04,05 testing shall be performed with both anode terminals 2 and 3 tied together.

2.9 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.



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APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from	Special In-process Control Internal Visual Inspection.
Production Control-	Wedge bonds equal to 1.1 wire diameters are acceptable for bonding with a
Chart F2	V-Groove tool.